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## HIGH-PERFORMANCE CONSUMER ELECTRONICS BROADCAST RADIO RECEIVER AND HD RADIO TUNER

### Features

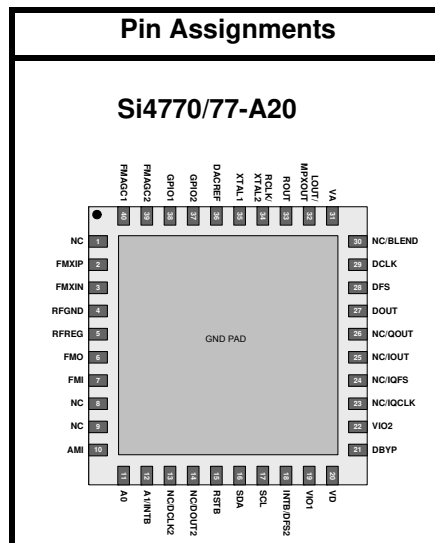
- Worldwide FM band support (64–108 MHz)
- Worldwide AM band support (520–1710 kHz)
- AM/FM HD Radio support (Si4777 only)
- Comprehensive signal quality metrics: RSSI, SNR, multipath interference, frequency offset, adjacent channel RSSI, frequency deviation, and image RSSI
- Advanced patented RDS soft-decision decoder
- Advanced, patented FM channel equalizer for multipath interference
- Dynamic AM/FM channel bandwidth control
- Programmable AM/FM soft mute
- FM stereo-mono blend
- FM hi-blend control
- AM/FM hi-cut control
- AM lo-cut filter
- L/R analog and digital (I<sup>2</sup>S) audio outputs
- Digital Low-IF architecture
- Frequency synthesizer with fully integrated PLL-VCO
- Fully integrated AM/FM front-end including high performance LNA, AGC with integrated resistor and capacitor banks, and RF and IF peak detectors
- Integrated crystal oscillator
- Digital (I<sup>2</sup>S) Zero-IF AM/FM I/Q outputs (Si4777 only)
- 1.2 to 5 V power supplies
- QFN 40-pin, 6x6x0.85 mm
  - Pb-free/RoHS compliant

### Applications

- Audio/video receivers
- Consumer electronics
- Boom boxes
- Home theater systems

### Description

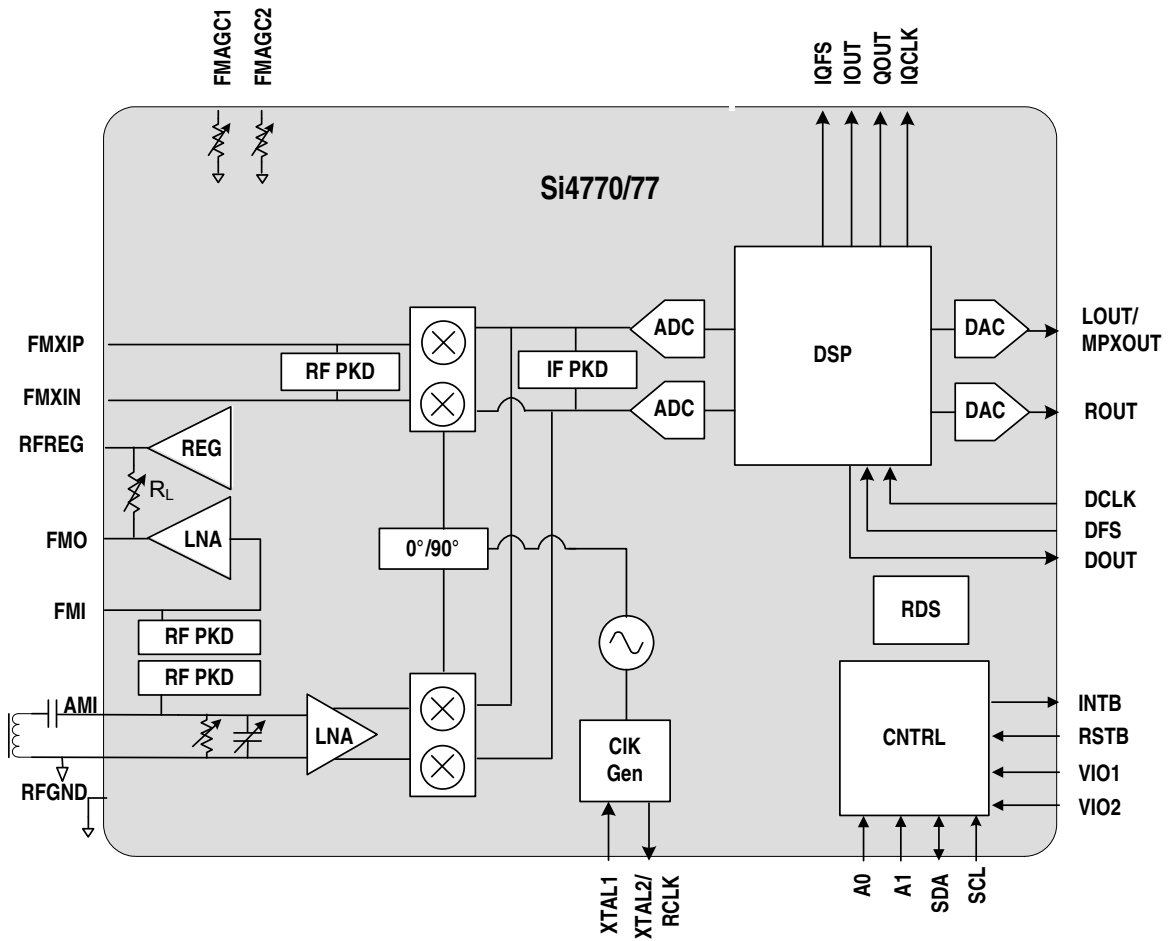
The Si4770/77-A20 broadcast receiver and HD Radio tuner (Si4777 only) employs an advanced, proven digital low-IF architecture to bring outstanding receiver performance to high-performance consumer electronics.



Patents pending

# Si4770/77-A20

## Functional Block Diagram



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## 1. Electrical Specifications

**Table 1. Recommended Operation Conditions\***

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Analog Supply Voltage	$V_A$	—	4.5	5	5.5	V
Digital Supply Voltage	$V_D$	—	2.7	3.3	3.6	V
Interface Supply Voltage	$V_{IO1}$	—	1.7	3.3	3.6	V
	$V_{IO2}$	—	1.2	3.3	3.6	V

**\*Note:** All minimum and maximum specifications are guaranteed and apply across the recommended operating conditions. Typical values apply at  $V_D = 3.3$  V,  $V_{IO1} = 3.3$  V,  $V_{IO2} = 3.3$  V,  $V_A = 5$  V, and 25 °C unless otherwise stated. Parameters are tested in production unless otherwise stated.

**Table 2. DC Characteristics**

( $T_{AMB} = -40$  to 85 °C,  $V_A = 4.5$  to 5.5 V,  $V_D = 2.7$  to 3.6 V,  $V_{IO1} = 1.7$  to 3.6 V,  $V_{IO2} = 1.2$  to 3.6 V)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>FM Mode</b>						
Total Supply Power			671	850	1049	mW
$V_A$ Supply Current	$I_{VA}$		121	130	139	mA
$V_D$ Supply Current	$I_{VD}$		47	60	79	mA
$V_A$ Supply Power Down Current	$I_{VA}$		20	90	170	$\mu$ A
$V_D$ Supply Power Down Current	$I_{VD}$		5	20	50	$\mu$ A
<b>AM Mode</b>						
Total Supply Power			707	900	1100	mW
$V_A$ Supply Current	$I_{VA}$		129	140	147	mA
$V_D$ Supply Current	$I_{VD}$		47	60	81	mA
$V_A$ Supply Power Down Current	$I_{VA}$		20	90	170	$\mu$ A
$V_D$ Supply Power Down Current	$I_{VD}$		5	20	50	$\mu$ A

**\*Note:** See "7. I2C Control Bus" on page 44.

**Table 2. DC Characteristics (Continued)**(T<sub>AMB</sub> = -40 to 85 °C, V<sub>A</sub> = 4.5 to 5.5 V, V<sub>D</sub> = 2.7 to 3.6 V, V<sub>IO1</sub> = 1.7 to 3.6 V, V<sub>IO2</sub> = 1.2 to 3.6 V)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Interface Supplies</b>						
V <sub>IO1</sub> Supply Current	I <sub>VIO1</sub>		0.1	0.5	0.82	mA
V <sub>IO2</sub> Supply Current	I <sub>VIO2</sub>		0.1	0.2	0.5	mA
V <sub>IO1</sub> Supply Power Down Current*	I <sub>PD</sub>		150	250	420	μA
V <sub>IO2</sub> Supply Power Down Current*	I <sub>PD</sub>		5	20	150	μA
<b>Inputs Pins SCL, SDA, RSTB, A0, A1</b>						
High Level Input Voltage	V <sub>IH</sub>		0.7 x V <sub>IO1</sub>	—	—	V
Low Level Input Voltage	V <sub>IL</sub>		—	—	0.3xV <sub>IO1</sub>	V
High Level Input Current	I <sub>IH</sub>	V <sub>IN</sub> = V <sub>IO1</sub> = 3.6 V	-10	—	10	μA
Low Level Input Current	I <sub>IL</sub>	V <sub>IN</sub> = 0 = V, V <sub>IO1</sub> = 3.6 V	-10	—	10	μA
<b>Input Pins DCLK, DFS</b>						
High Level Input Voltage	V <sub>IH</sub>		0.7 x V <sub>IO2</sub>	—	—	V
Low Level Input Voltage	V <sub>IL</sub>		—	—	0.3 x V <sub>IO2</sub>	V
High Level Input Current	I <sub>IH</sub>	V <sub>IN</sub> = V <sub>IO2</sub> = 3.6 V	-10	—	10	μA
Low Level Input Current	I <sub>IL</sub>	V <sub>IN</sub> = 0 V, V <sub>IO2</sub> = 3.6 V	-10	—	10	μA
<b>Input Pins GPIO1, GPIO2</b>						
High Level Input Voltage	V <sub>IH</sub>	GPIO1 and GPIO2 are internally regulated at 3.6 V	2.52	—	—	V
Low Level Input Voltage	V <sub>IL</sub>		—	—	1.08	V
High Level Input Current	I <sub>IH</sub>	V <sub>IN</sub> = 3.6 V	-10	—	10	μA
Low Level Input Current	I <sub>IL</sub>	V <sub>IN</sub> = 0 V	-10	—	10	μA
<b>Output Pins INTB</b>						
High Level Output Voltage	V <sub>OH</sub>	Output is common drain output with internal 10 kΩ pull-up to V <sub>IO1</sub>	0.8xV <sub>IO1</sub>	—	—	V
Low Level Output Voltage	V <sub>OL</sub>	I <sub>OUT</sub> = -500 μA	—	—	0.2xV <sub>IO1</sub>	V
<b>*Note:</b> See "7. I2C Control Bus" on page 44.						

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**Table 2. DC Characteristics (Continued)**

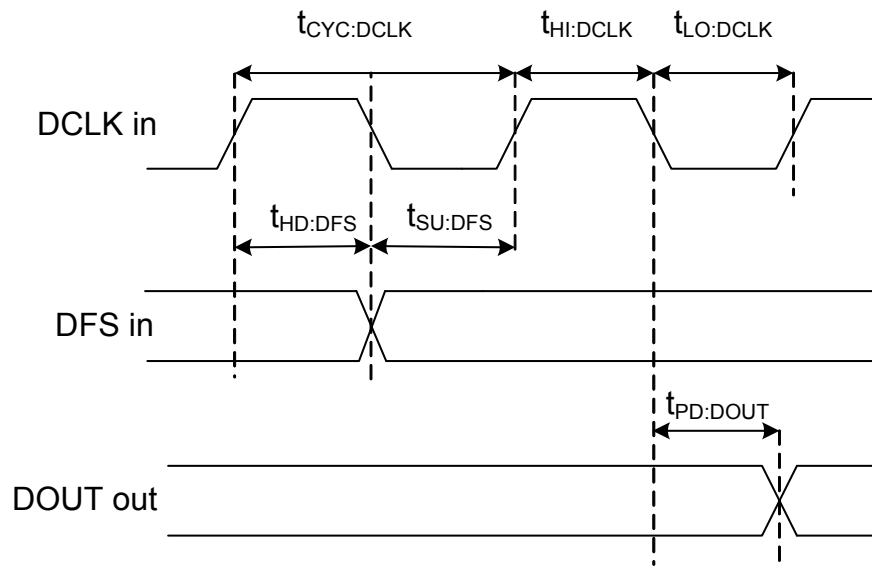
( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Output Pins SDA</b>						
High Level Output Voltage	$V_{OH}$	Output is common drain output with external $4.7$ k $\Omega$ pull-up to $V_{IO1}$	$0.8 \times V_{IO1}$	—	—	V
Low Level Output Voltage	$V_{OL}$	$I_{OUT} = -500$ $\mu$ A	—	—	$0.2 \times V_{IO1}$	V
<b>Output Pins GPIO1, GPIO2</b>						
High Level Output Voltage	$V_{OH}$	GPIO1 and GPIO2 are internally regulated at $3.6$ V, $I_{OUT} = +500$ $\mu$ A	2.88	—	—	V
Low Level Output Voltage	$V_{OL}$	$I_{OUT} = -500$ $\mu$ A	—	—	0.72	V
<b>Output Pins IQCLK, IQFS, IOOUT, QOUT, DFS, DCLK, DOUT</b>						
High Level Output Voltage	$V_{OH}$	$I_{OUT} = 500$ $\mu$ A	$0.8 \times V_{IO2}$	—	—	V
Low Level Output Voltage	$V_{OL}$	$I_{OUT} = -500$ $\mu$ A	—	—	$0.2 \times V_{IO2}$	V
<b>*Note:</b> See "7. I2C Control Bus" on page 44.						

**Table 3. Digital Audio Interface Characteristics\***(T<sub>AMB</sub> = -40 to 85 °C, V<sub>A</sub> = 4.5 to 5.5 V, V<sub>D</sub> = 2.7 to 3.6 V, V<sub>IO1</sub> = 1.7 to 3.6 V, V<sub>IO2</sub> = 1.2 to 3.6 V)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DCLK Input Cycle Time	t <sub>CYC:DCLK</sub>		70	—	—	ns
DCLK Input Pulse Width High	t <sub>HI:DCLK</sub>		0.4 x t <sub>CYC:DCLK</sub>	—	0.6 x t <sub>CYC:DCLK</sub>	ns
DCLK Input Pulse Width Low	t <sub>LO:DCLK</sub>		0.4 x t <sub>CYC:DCLK</sub>	—	0.6 x t <sub>CYC:DCLK</sub>	ns
DFS Setup Time	t <sub>SU:DFS</sub>		10	—	—	ns
DFS Hold Time	t <sub>HD:DFS</sub>		5	—	—	ns
DOUT ouTput Delay	t <sub>PD:DOUT</sub>		0	—	35	ns
Capacitive Loading	C <sub>B</sub>	V <sub>IO2</sub> ≤ 1.33 V	—	—	10	pF
		V <sub>IO2</sub> > 1.33 V	—	—	15	

**\*Note:** Guaranteed by characterization.

**Figure 1. Digital Audio**



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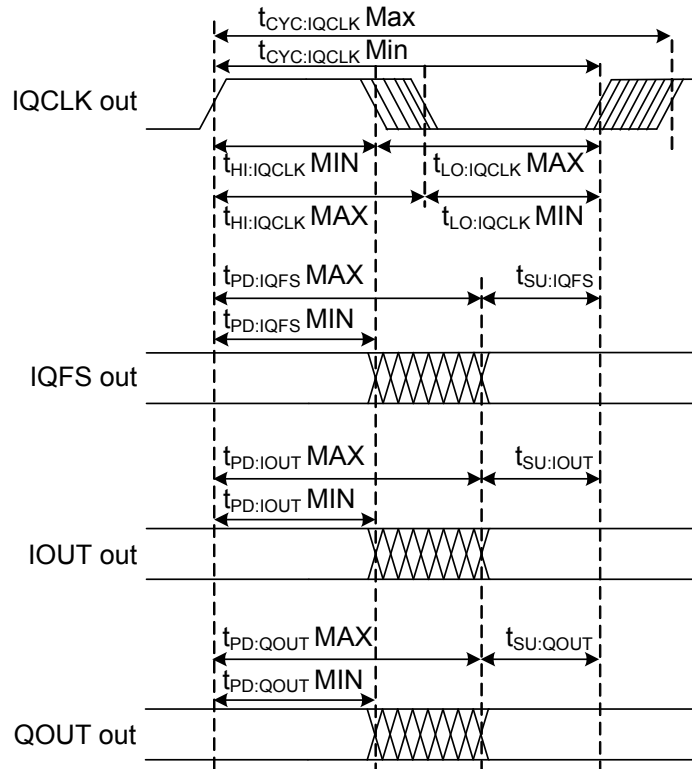
**Table 4. Digital Zero-IF I/Q Interface Characteristics (Si4777 Only)<sup>1</sup>**

( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
IQCLK Output Cycle Time	$t_{CYC:IQCLK}$		0.8 x per	per <sup>2</sup>	1.2 x per	ns
IQCLK Output Pulse Width High	$t_{HI:IQCLK}$		0.22 x per	—	0.59 x per	ns
IQCLK Output Pulse Width Low	$t_{LO:IQCLK}$		0.41 x per	—	0.78 x per	ns
IQFS Output Delay	$t_{PD:IQFS}$		0	—	(0.5 x per) + 18	ns
IQFS Output Setup to IQCLK Rise <sup>3</sup>	$t_{SU:IQFS}$		(0.5 x per) – 18	—	—	ns
IOOUT Output Delay	$t_{PD:IOOUT}$		0	—	(0.5 x per) + 18	ns
QOUT Output Delay	$t_{PD:QOUT}$		0	—	(0.5 x per) + 18	ns
IOOUT Output Setup to IQCLK rise <sup>3</sup>	$t_{SU:IOOUT}$		(0.5 x per) – 18	—	—	ns
QOUT Output Setup to IQCLK Rise <sup>3</sup>	$t_{SU:QOUT}$		(0.5 x per) – 18	—	—	ns

**Notes:**

1. Guaranteed by characterization.
2. per is the IQCLK I/Q bit clock period. Refer to Table 15 on page 35 for IQCLK bit clock frequencies.
3. Minimum time the Si4770/77-A20 will produce between valid output and the next rising edge of IQCLK



**Figure 2. Digital Zero-IF I/Q**

Table 5. Reference Clock and Crystal Characteristics

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Reference Clock, Pin RCLK</b>						
RCLK Supported Frequencies			—	36.4 37.8 37.209375	—	MHz
RCLK Frequency Tolerance			-100	—	100	ppm
<b>RCLK = 36.4 MHz, 37.8 MHz, 37.209375 MHz</b>						
Phase Noise		100 Hz offset	—	—	-86	dBc/Hz
		1 kHz offset	—	—	-101	dBc/Hz
		10 kHz offset	—	—	-108	dBc/Hz
		≥ 100 kHz offset	—	—	-122	dBc/Hz
Input Capacitance			—	7	—	pF
Input Voltage		AC coupling capacitor = 1 $\mu$ F Square wave input			400	mV <sub>PP</sub>
		AC coupling capacitor = 1 $\mu$ F Sine wave input	300	—	900	mV <sub>PP</sub>
<b>Crystal Oscillator, Pins XTAL1, XTAL2</b>						
Crystal Frequency			—	36.4 37.8 37.209375	—	MHz
Crystal Frequency Tolerance			-100	—	100	ppm
Load Capacitance, Programmable, Each Pin to GND			5	—	21.8	pF

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**Table 6. I<sup>2</sup>C Control Interface Characteristics**

(T<sub>AMB</sub> = -40 to 85 °C, V<sub>A</sub> = 4.5 to 5.5 V, V<sub>D</sub> = 2.7 to 3.6 V, V<sub>IO1</sub> = 1.7 to 3.6 V, V<sub>IO2</sub> = 1.2 to 3.6 V)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Pins SCL, SDA</b>						
SCL Frequency	f <sub>SCL</sub>		0	—	400	kHz
SCL Low Time	t <sub>LOW</sub>		1.3	—	—	μs
SCL High Time	t <sub>HIGH</sub>		0.6	—	—	μs
SCL Input to SDA ↓ Setup (START)	t <sub>SU:STA</sub>		0.6	—	—	μs
SCL Input from SDA ↓ Hold (START)	t <sub>HD:STA</sub>		0.6	—	—	μs
SDA Input to SCL ↑ Setup	t <sub>SU:DAT</sub>		100	—	—	ns
SDA Input from SCL ↓ Hold	t <sub>HD:DAT</sub>		0	—	900	ns
SDA Output Delay	t <sub>PD:DAT</sub>		300	—	900	ns
SCL Input to SDA ↑ Setup (STOP)	t <sub>SU:STO</sub>		0.6	—	—	μs
STOP to START Time	t <sub>BUF</sub>		1.3	—	—	μs
SDA Output Fall Time	t <sub>f:OUT</sub>		$20 + 0.1 \frac{C_B}{1\text{pF}}$	—	250	ns
SDA Input, SCL Rise/Fall Time	t <sub>f:IN</sub> , t <sub>r:IN</sub>		$20 + 0.1 \frac{C_B}{1\text{pF}}$	—	300	ns
Capacitive Loading	C <sub>B</sub>		—	—	50	pF
Pulse Width Rejected by Input Filter	t <sub>SP</sub>		—	—	50	ns

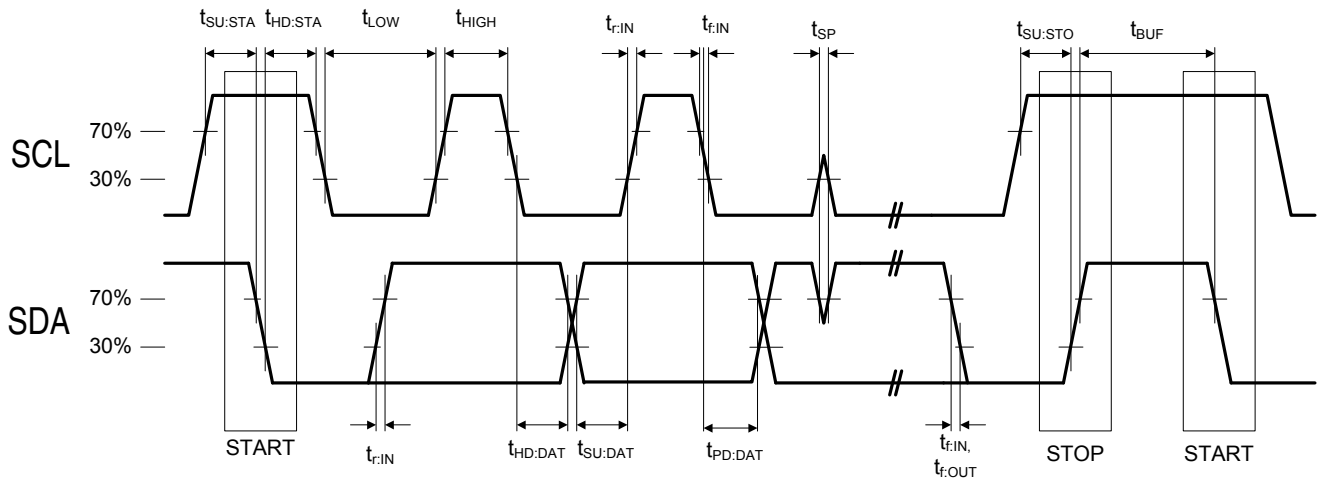


Figure 3. I<sup>2</sup>C Control Interface Read and Write Timing Parameters

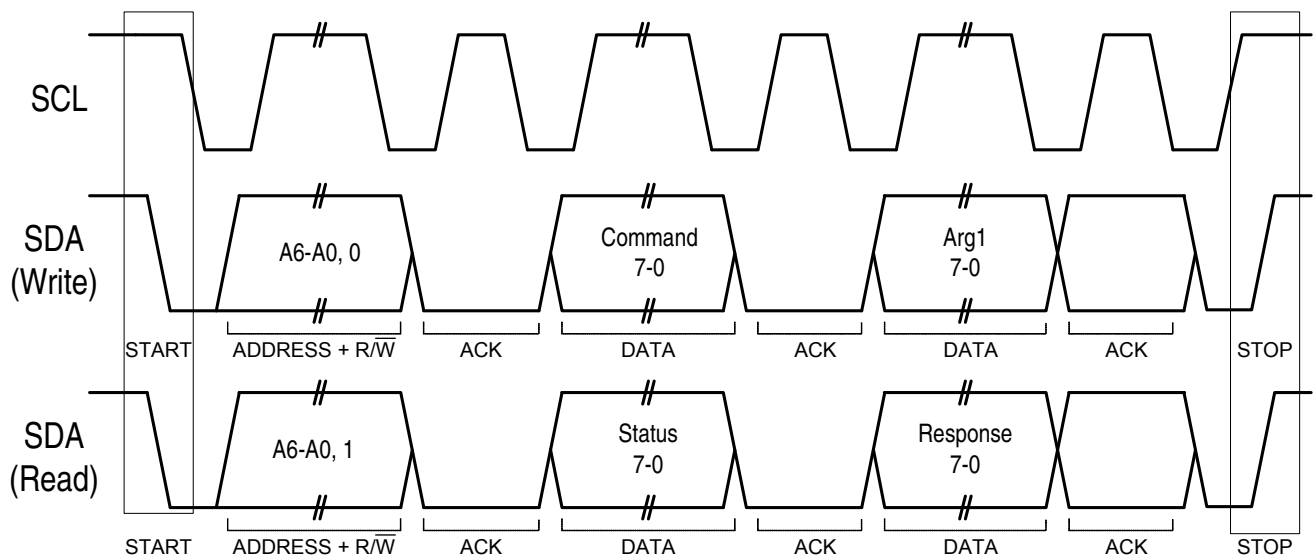


Figure 4. I<sup>2</sup>C Control Interface Read and Write Timing Diagram

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**Table 7. FM Receiver Characteristics**

( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V. Typical values measured at  $T_{AMB} = 25$  °C, FM modulation (L = R),  $F_{MOD} = 1$  kHz,  $F_{DEV} = 22.5$  kHz, Deemphasis =  $75$   $\mu$ sec, RF level =  $60$  dB $\mu$ V, and  $F_{RF} = 98$  MHz in application circuit unless otherwise specified)

Parameter	Test Condition	Min	Typ	Max	Unit
Input Frequency		64	—	108	MHz
Frequency Step Resolution		10	—	200	kHz
Powerup Time <sup>1,2</sup>	RCLK or Crystal = 36.4 MHz, 37.8 MHz, 37.209375 MHz	—	—	100	ms
Tune time <sup>1</sup>		—	1.5	—	ms
Seek Time/Channel <sup>1</sup>	At LOUT and ROUT pins	—	20	—	ms
Max Frequency Deviation <sup>1</sup>	Audio THD <1%, over-deviation handling enabled	—	150	—	kHz
RF AGC Range		—	40	—	dB
AGC Gain Resolution <sup>3</sup>		—	2	—	dB
RF AGC Threshold Accuracy <sup>3</sup>			2	—	dB
IF AGC Threshold Accuracy <sup>3</sup>			1	—	dB

**Following FM Receiver Specifications Refer to Si4770/77-A20 Application Circuit Input**

IP3 <sup>6</sup>	Blockers at 400/800 kHz offset AGC disabled (Max RF gain)	115	117	—	dB $\mu$ V
Sensitivity <sup>6</sup>	Audio SINAD = 26 dB AGC disabled (Max RF gain)	—	-3.5	-2	dB $\mu$ V
Image Rejection <sup>1</sup>	Deviation = 22.5 kHz	65	70	—	dB
Adjacent Channel Rejection <sup>1,6</sup>	Audio SINAD = 26 dB Desired = 40dB $\mu$ V, $F_{MOD} = 1$ kHz, $F_{DEV} = 22.5$ kHz Undesired at $\pm 100$ kHz offset, $F_{MOD} = 400$ Hz, $F_{DEV} = 22.5$ kHz	63	65	—	dB

**Notes:**

1. Guaranteed by characterization.
2. Measured at  $T_{AMB} = 25$  °C.
3. Guaranteed by design.
4. IP3 measured at the FMXIP and FMXIN pins reflects IP3 for mixer stage and all subsequent downstream blocks.
5. Refer to FM test circuit in Figure 5.
6. No A-weighting. Noise integrated from 30 Hz to 15 kHz for audio SINAD and SNR measurements.
7. Input resistance is software configurable.
8. IP3 measured at the FMI input pin reflects IP3 for FMI LNA stage.
9. RDS Synchronization Persistence is the minimum RF level at which the tuner loses synchronization to the RDS PI code as the RF level decreases from high to low levels.
10. RDS Synchronization Stability is the minimum RF level at which the tuner achieves synchronization to the RDS PI code as the RF level increases from low to high levels.
11. Noise integrated from 30 Hz to 120 kHz for audio SINAD and SNR measurements.

**Table 7. FM Receiver Characteristics (Continued)**

( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V. Typical values measured at  $T_{AMB} = 25$  °C, FM modulation (L = R),  $F_{MOD} = 1$  kHz,  $F_{DEV} = 22.5$  kHz, Deemphasis =  $75$   $\mu$ sec, RF level =  $60$  dB $\mu$ V, and  $F_{RF} = 98$  MHz in application circuit unless otherwise specified)

Parameter	Test Condition	Min	Typ	Max	Unit
Alternate Channel Rejection <sup>6</sup>	Audio SINAD = 26 dB Desired = 40 dB $\mu$ V, $F_{MOD} = 1$ kHz, $F_{DEV} = 22.5$ kHz Undesired at $\pm 200$ kHz offset, $F_{MOD} = 400$ Hz, $F_{DEV} = 22.5$ kHz	65	72	—	dB
THD	$F_{DEV} = 75$ kHz	—	0.05	0.1	%
Mono (S+N)/N <sup>6</sup>		66	75	—	dB
Stereo (S+N)/N <sup>6</sup>	Stereo modulation (L = 1, R = 0), deviation = 67.5 kHz, pilot deviation = 6.75 kHz	64	70	—	dB
AM Suppression <sup>1</sup>	AM: $m = 0.3/F_{mod} = 1$ kHz, RF level = 60 dB $\mu$ V	50	55	—	dB
De-Emphasis Time Constant <sup>3</sup>		70	75	80	$\mu$ sec
		45	50	54	$\mu$ sec
L/R Imbalance	Deviation = 75 kHz	-1	—	1	dB
Stereo Separation	Stereo modulation (L = 1, R = 0), Deviation = 67.5 kHz, pilot deviation = 6.75 kHz	40	43	—	dB
Stereo THD	Stereo modulation (L = 1, R = 0), Deviation = 67.5 kHz, pilot deviation = 6.75 kHz	—	0.1	0.2	%
Pilot Signal Rejection <sup>1</sup>	Stereo modulation (L = 1, R = 0), Deviation = 67.5 kHz, pilot deviation = 6.75 kHz	—	55	—	dB
RDS Sensitivity <sup>1</sup>	$\Delta f = 2$ kHz, RDS BLER < 5%	—	13	14.5	dB $\mu$ V
RDS Synchronization Time <sup>1</sup>	$\Delta f = 2$ kHz RF input = 60 dB $\mu$ V	—	70	—	ms
RDS PI Lock Time <sup>1</sup>	$\Delta f = 2$ kHz RF input = 60 dB $\mu$ V	—	85	—	ms

**Notes:**

1. Guaranteed by characterization.
2. Measured at  $T_{AMB} = 25$  °C.
3. Guaranteed by design.
4. IP3 measured at the FMXIP and FMXIN pins reflects IP3 for mixer stage and all subsequent downstream blocks.
5. Refer to FM test circuit in Figure 5.
6. No A-weighting. Noise integrated from 30 Hz to 15 kHz for audio SINAD and SNR measurements.
7. Input resistance is software configurable.
8. IP3 measured at the FMI input pin reflects IP3 for FMI LNA stage.
9. RDS Synchronization Persistence is the minimum RF level at which the tuner loses synchronization to the RDS PI code as the RF level decreases from high to low levels.
10. RDS Synchronization Stability is the minimum RF level at which the tuner achieves synchronization to the RDS PI code as the RF level increases from low to high levels.
11. Noise integrated from 30 Hz to 120 kHz for audio SINAD and SNR measurements.

# Si4770/77-A20

**Table 7. FM Receiver Characteristics (Continued)**

( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V. Typical values measured at  $T_{AMB} = 25$  °C, FM modulation (L = R),  $F_{MOD} = 1$  kHz,  $F_{DEV} = 22.5$  kHz, Deemphasis =  $75$   $\mu$ sec, RF level =  $60$  dB $\mu$ V, and  $F_{RF} = 98$  MHz in application circuit unless otherwise specified)

Parameter	Test Condition	Min	Typ	Max	Unit
<b>FM Mixer Inputs: Pins FMXIP, FMXIN</b>					
Maximum RF Input Voltage <sup>3</sup>	1 dB compression point of mixer	—	112	—	dB $\mu$ V
Mixer Input Resistance <sup>3</sup>		—	8	—	k $\Omega$
Mixer Input Capacitance <sup>3</sup>		—	6	—	pF
IP3 <sup>4,5,6</sup>	Blockers at 400/800 kHz offset, Max Gain (AGC disabled)	—	123	—	dB $\mu$ V
Sensitivity <sup>5,6</sup>	Audio SINAD = 26 dB Max Gain (AGC disabled)	—	3.5	—	dB $\mu$ V
<b>FM Resistor Banks: FMAGC1, FMAGC2</b>					
FMAGC1 Min		—	2.5	—	$\Omega$
FMAGC1 Max		—	800	—	$\Omega$
FMAGC1 Step Size	Maximum parallel resistance change	—	800	—	$\Omega$
FMAGC2 Min		—	2.5	—	$\Omega$
FMAGC2 Max		—	800	—	$\Omega$
FMAGC2 Step Size	Maximum parallel resistance change	—	800	—	$\Omega$
<b>FM LNA: Pins FMI, FMO</b>					
<b>Single Receiver Mode</b>					
FMI Input Resistance <sup>3,7</sup>		—	50	—	$\Omega$
FMI Input Capacitance <sup>3</sup>		—	2	—	pF
FMI Return Loss <sup>3</sup>	64 MHz < F < 108 MHz	—	15	—	dB
FMI Input Referred Noise <sup>3</sup>		—	0.73	—	nV/ $\sqrt{\text{Hz}}$
FMI LNA IP3 <sup>3,8</sup>	Blockers at 400/800 kHz offset, Max Gain	—	128	—	dB $\mu$ V
<b>Notes:</b>					
<ol style="list-style-type: none"> <li>1. Guaranteed by characterization.</li> <li>2. Measured at <math>T_{AMB} = 25</math> °C.</li> <li>3. Guaranteed by design.</li> <li>4. IP3 measured at the FMXIP and FMXIN pins reflects IP3 for mixer stage and all subsequent downstream blocks.</li> <li>5. Refer to FM test circuit in Figure 5.</li> <li>6. No A-weighting. Noise integrated from 30 Hz to 15 kHz for audio SINAD and SNR measurements.</li> <li>7. Input resistance is software configurable.</li> <li>8. IP3 measured at the FMI input pin reflects IP3 for FMI LNA stage.</li> <li>9. RDS Synchronization Persistence is the minimum RF level at which the tuner loses synchronization to the RDS PI code as the RF level decreases from high to low levels.</li> <li>10. RDS Synchronization Stability is the minimum RF level at which the tuner achieves synchronization to the RDS PI code as the RF level increases from low to high levels.</li> <li>11. Noise integrated from 30 Hz to 120 kHz for audio SINAD and SNR measurements.</li> </ol>					

**Table 7. FM Receiver Characteristics (Continued)**

( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V. Typical values measured at  $T_{AMB} = 25$  °C, FM modulation (L = R),  $F_{MOD} = 1$  kHz,  $F_{DEV} = 22.5$  kHz, Deemphasis =  $75$   $\mu$ sec, RF level =  $60$  dB $\mu$ V, and  $F_{RF} = 98$  MHz in application circuit unless otherwise specified)

Parameter	Test Condition	Min	Typ	Max	Unit
FMO Output Resistance <sup>3</sup>	Nominal FMI to FMO gain = 8 dB, Source load = 50 $\Omega$	—	125	—	$\Omega$
FMO Output Capacitance <sup>3</sup>		—	2	—	pF
<b>Dual Receiver Mode</b>					
FMI Input Resistance <sup>7,3</sup>		—	100	—	$\Omega$
FMI Input Capacitance <sup>3</sup>		—	1.5	—	pF
FMI Return Loss <sup>3</sup>	64 MHz < F < 108 MHz	—	15	—	dB
FMI Input Referred Noise <sup>3</sup>		—	1.20	—	nV/ $\sqrt{\text{Hz}}$
FMI LNA IP <sub>3</sub> <sup>3,8</sup>	Blockers at 400/800 kHz offset, Max Gain	—	126	—	dB $\mu$ V
FMO Output Resistance <sup>3</sup>	Nominal FMI to FMO gain = 8dB, Source load = 50 $\Omega$	—	250	—	$\Omega$
FMO Output Capacitance <sup>3</sup>		—	2	—	pF
<b>Audio Outputs: Pins LOUT and ROUT</b>					
Audio Frequency Response Low <sup>1,2</sup>	$\pm 3$ dB	—	—	30	Hz
Audio Frequency Response High <sup>1,2</sup>	$\pm 3$ dB	15	—	—	kHz
Output Load Resistance <sup>3</sup>	At LOUT and ROUT pins	10 k	—	—	$\Omega$
Output Load Capacitance <sup>3</sup>	At LOUT and ROUT pins	—	—	50	pF
Output Voltage	Deviation = 22.5 kHz	99	112	125	mVRMS
Power Supply Rejection Ratio (PSRR) <sup>3</sup>	100 Hz ripple on power supply lines. Ripple voltage = 100 mV <sub>PP</sub> of power supply voltage	—	45	—	dB

**Notes:**

1. Guaranteed by characterization.
2. Measured at  $T_{AMB} = 25$  °C.
3. Guaranteed by design.
4. IP<sub>3</sub> measured at the FMXIP and FMXIN pins reflects IP<sub>3</sub> for mixer stage and all subsequent downstream blocks.
5. Refer to FM test circuit in Figure 5.
6. No A-weighting. Noise integrated from 30 Hz to 15 kHz for audio SINAD and SNR measurements.
7. Input resistance is software configurable.
8. IP<sub>3</sub> measured at the FMI input pin reflects IP<sub>3</sub> for FMI LNA stage.
9. RDS Synchronization Persistence is the minimum RF level at which the tuner loses synchronization to the RDS PI code as the RF level decreases from high to low levels.
10. RDS Synchronization Stability is the minimum RF level at which the tuner achieves synchronization to the RDS PI code as the RF level increases from low to high levels.
11. Noise integrated from 30 Hz to 120 kHz for audio SINAD and SNR measurements.



# Si4770/77-A20

**Table 7. FM Receiver Characteristics (Continued)**

( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V. Typical values measured at  $T_{AMB} = 25$  °C, FM modulation (L = R),  $F_{MOD} = 1$  kHz,  $F_{DEV} = 22.5$  kHz, Deemphasis =  $75$   $\mu$ sec, RF level =  $60$  dB $\mu$ V, and  $F_{RF} = 98$  MHz in application circuit unless otherwise specified)

Parameter	Test Condition	Min	Typ	Max	Unit
<b>FM MPX Output: Pins MPXOUT</b>					
Output Voltage <sup>1</sup>	$F_{RF} = 83$ MHz, RF level = $65$ dB $\mu$ V, $F_{DEV} = 3$ kHz, $F_{MOD} = 76$ kHz unless otherwise noted	14	16	—	mVRMS
Output Load Resistance <sup>3</sup>		—	10	—	k $\Omega$
Output Load Capacitance <sup>3</sup>		—	50	—	pF
PSRR <sup>3</sup>	100 Hz ripple on power supply lines. Ripple voltage = $100$ mV <sub>PP</sub> of power supply voltage	—	45	—	dB
Bandwidth <sup>1</sup>		110	—	—	kHz
<b>Following FM MPX Specifications Refer to Si4770/77-A20 Application Circuit</b>					
(S+N)/N <sup>1,11</sup>	$F_{RF} = 83$ MHz, RF level = $65$ dB $\mu$ V, $F_{DEV} = 3$ kHz, $F_{MOD} = 76$ kHz unless otherwise noted	25	30	—	dB
Sensitivity <sup>1,11</sup>	$F_{RF} = 83$ MHz, $F_{DEV} = 3$ kHz, $F_{MOD} = 76$ kHz unless otherwise noted, SINAD = $5$ dB	—	19	25	dB $\mu$ V
<b>Notes:</b>					
<ol style="list-style-type: none"> <li>1. Guaranteed by characterization.</li> <li>2. Measured at <math>T_{AMB} = 25</math> °C.</li> <li>3. Guaranteed by design.</li> <li>4. IP3 measured at the FMXIP and FMXIN pins reflects IP3 for mixer stage and all subsequent downstream blocks.</li> <li>5. Refer to FM test circuit in Figure 5.</li> <li>6. No A-weighting. Noise integrated from <math>30</math> Hz to <math>15</math> kHz for audio SINAD and SNR measurements.</li> <li>7. Input resistance is software configurable.</li> <li>8. IP3 measured at the FMI input pin reflects IP3 for FMI LNA stage.</li> <li>9. RDS Synchronization Persistence is the minimum RF level at which the tuner loses synchronization to the RDS PI code as the RF level decreases from high to low levels.</li> <li>10. RDS Synchronization Stability is the minimum RF level at which the tuner achieves synchronization to the RDS PI code as the RF level increases from low to high levels.</li> <li>11. Noise integrated from <math>30</math> Hz to <math>120</math> kHz for audio SINAD and SNR measurements.</li> </ol>					

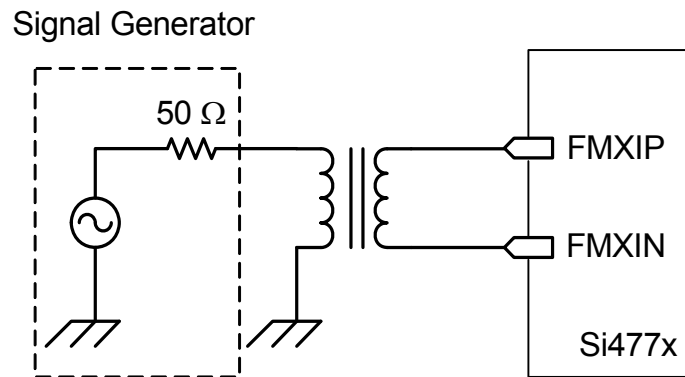


Figure 5. FM Test Circuit for Mixer Input IP3 and Sensitivity Measurement

Table 8. AM Receiver Characteristics

( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V. Typical values measured at  $T_{AMB} = 25$  °C, AM modulation = 30%,  $F_{MOD} = 1$  kHz, RF level =  $74$  dB $\mu$ V, and  $F_{RF} = 1$  MHz unless otherwise specified)

Parameter	Test Condition	Min	Typ	Max	Unit
Input Frequency		520	—	1710	kHz
Frequency Step Resolution		1	—	10	kHz
Powerup Time <sup>1,2</sup>	RCLK or Crystal = 36.4 MHz, 37.8 MHz, 37.209375 MHz	—	—	100	ms
Tune Time <sup>1</sup>		—	15	—	ms
Seek Time/Channel <sup>1</sup>	At LOUT and ROUT pins	—	55	—	ms
Maximum RF Input Voltage <sup>1,2</sup>	Mod = 90%, Fmod = 1 kHz, SINAD = 57 dB	—	93	—	dB $\mu$ V
Image Rejection <sup>1,3</sup>		68	72	—	dB
Adjacent Channel Rejection <sup>1,3</sup>	SINAD = 20 dB Desired = 40 dB $\mu$ V, $F_{MOD} = 1$ kHz, MOD = 30% Undesired at $\pm 9$ kHz offset, $F_{MOD} = 400$ Hz, MOD = 30%	57	62	—	dB
Alternate Channel Rejection <sup>1,3</sup>	SINAD = 20 dB Desired = 40dB $\mu$ V, $F_{MOD} = 1$ kHz, MOD = 30% Undesired at $\pm 18$ kHz offset, $F_{MOD} = 400$ Hz, MOD = 30%	59	62	—	dB
IP3 <sup>1,3</sup>	Blockers at 40/80 kHz, AGC disabled (Max gain)	110	120	—	dB $\mu$ V

**Notes:**

1. Guaranteed by characterization.
2. Measured at  $T_{AMB} = 25$  °C.
3. No A-weighting. Noise integrated from 30 Hz to 15 kHz for audio SINAD and SNR measurements.
4. Guaranteed by design.

# Si4770/77-A20

**Table 8. AM Receiver Characteristics (Continued)**

( $T_{AMB} = -40$  to  $85$  °C,  $V_A = 4.5$  to  $5.5$  V,  $V_D = 2.7$  to  $3.6$  V,  $V_{IO1} = 1.7$  to  $3.6$  V,  $V_{IO2} = 1.2$  to  $3.6$  V. Typical values measured at  $T_{AMB} = 25$  °C, AM modulation = 30%,  $F_{MOD} = 1$  kHz, RF level = 74 dB $\mu$ V, and  $F_{RF} = 1$  MHz unless otherwise specified)

Parameter	Test Condition	Min	Typ	Max	Unit
IP2 <sup>1,3</sup>	Desired = 700 kHz, Undesired = 1000 kHz, 1700 kHz AGC disabled (Max gain)	142	146	—	dB $\mu$ V
RF AGC Range		—	50	—	dB
AGC Step Resolution			2		dB
RF AGC Threshold Accuracy <sup>4</sup>		—	2	—	dB
IF AGC Threshold Accuracy <sup>4</sup>		—	2	—	dB
Sensitivity <sup>1,3</sup>	SINAD = 20 dB, AGC Disabled (Max RF Gain)	—	14	17	dB $\mu$ V EMF
THD <sup>1,3</sup>	Mod = 30%	—	0.1	—	%
	Mod = 90%	—	0.2	—	%
Audio SNR <sup>1,3</sup>	Mod = 30%	60	65	—	dB
Antenna Inductance <sup>3</sup>		180	—	540	$\mu$ H
<b>Audio Outputs: Pins LOUT and ROUT</b>					
Audio Output Resistance Load <sup>4</sup>		10k	—	—	$\Omega$
Audio Output Capacitance Load <sup>4</sup>	Single Ended	—	—	50	pF
Audio Output Voltage		96	108	121	mVRMS
PSRR at Audio Output Pins <sup>4</sup>	Ripple test should be for 100 Hz ripple on power supply lines Ripple voltage = 100 mV <sub>PP</sub> of power supply voltage	—	45	—	dB
<b>Notes:</b>					
1. Guaranteed by characterization.					
2. Measured at $T_{AMB} = 25$ °C.					
3. No A-weighting. Noise integrated from 30 Hz to 15 kHz for audio SINAD and SNR measurements.					
4. Guaranteed by design.					

Table 9. Thermal Conditions

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Ambient Temperature	$T_{AMB}$	—	-40	25	85	°C
Junction Temperature	$T_J$	—	—	—	115	°C
Delta from Junction to Ambient*	$\theta_{JA}$	—	—	27	—	°C/W

\*Note: The  $\theta_{JA}$  is layout-dependent, and, therefore, PCB layout must provide adequate heat-sink capability. The  $\theta_{JA}$  is specified assuming adequate ground plane.

Table 10. Absolute Maximum Ratings<sup>1</sup>

Parameter	Symbol	Min	Max	Unit
Analog Supply Voltage	$V_A$	-0.5	5.9	V
Digital Supply Voltage	$V_D$	-0.5	3.9	V
I/O 1 Supply Voltage	$V_{IO1}$	-0.5	3.9	V
I/O 2 Supply Voltage	$V_{IO2}$	-0.5	3.9	V
I/O 1 Input Current <sup>2</sup>	$I_{IN1}$	-10	10	μA
I/O 1 Input Voltage <sup>2</sup>	$V_{IN1}$	-0.3	$V_{IO1} + 0.3$	V
I/O 2 Input Current <sup>3</sup>	$I_{IN2}$	-10	10	μA
I/O 2 Input Voltage <sup>3</sup>	$V_{IN2}$	-0.3	$V_{IO2} + 0.3$	V
Operating Temperature	$T_{OP}$	-40	95	°C
Storage Temperature	$T_{STG}$	-55	150	°C
AM RF Input Level <sup>4</sup>	$V_{RFIN}$	-1	$V_A + 1$	V
AM RF Input Current <sup>4</sup>	$I_{RFIN}$	-100	100	mA
FM RF Input Level <sup>5</sup>	$V_{RFIN}$	-1	1	V
FM RF Input Current <sup>5</sup>	$I_{RFIN}$	-100	100	mA
HBM ESD	$V_{HBM}$	-2	2	kV
MM ESD	$V_{MM}$	-200	200	V
CDM ESD <sup>6</sup>	$V_{CDM}$	-500	500	V
CDM ESD <sup>7</sup>	$V_{CDM}$	-750	750	V

**Notes:**

1. Permanent device damage may occur if the absolute maximum ratings are exceeded. Functional operation should be restricted to the conditions as specified in the operational sections of this data sheet. Exposure beyond recommended operating conditions for extended periods may affect device reliability.
2. For input pins SCL, SDA, RSTB, A0, A1, GPIO1, GPIO2.
3. For input pins DCLK and DFS.
4. At RF input pins AM1.
5. At RF input pins FMXIN, FMXIP, FMI, FMAGC1, FMAGC2.
6. All pins.
7. Corner pins.

## 2. Typical Application Schematic

Figure 6 shows the proposed application schematic.

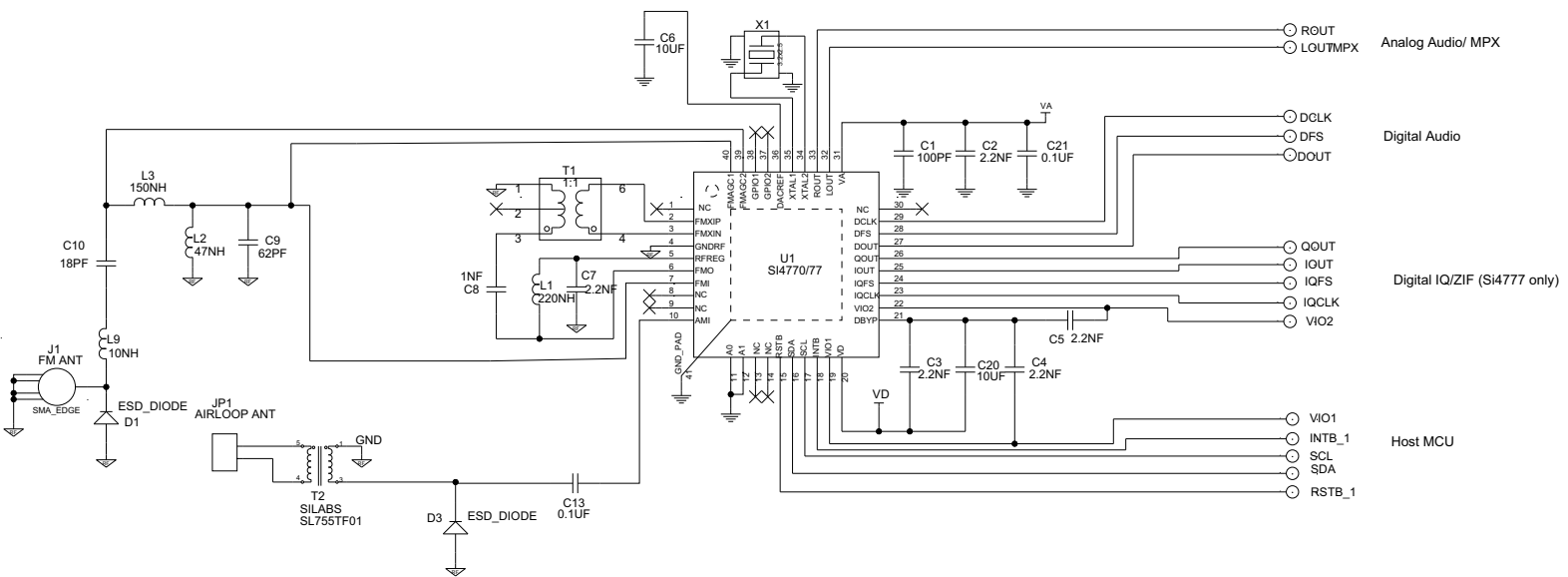


Figure 6. Application Circuit

### 3. Bill of Materials

Table 11. Si4770/77-A20 Bill of Materials

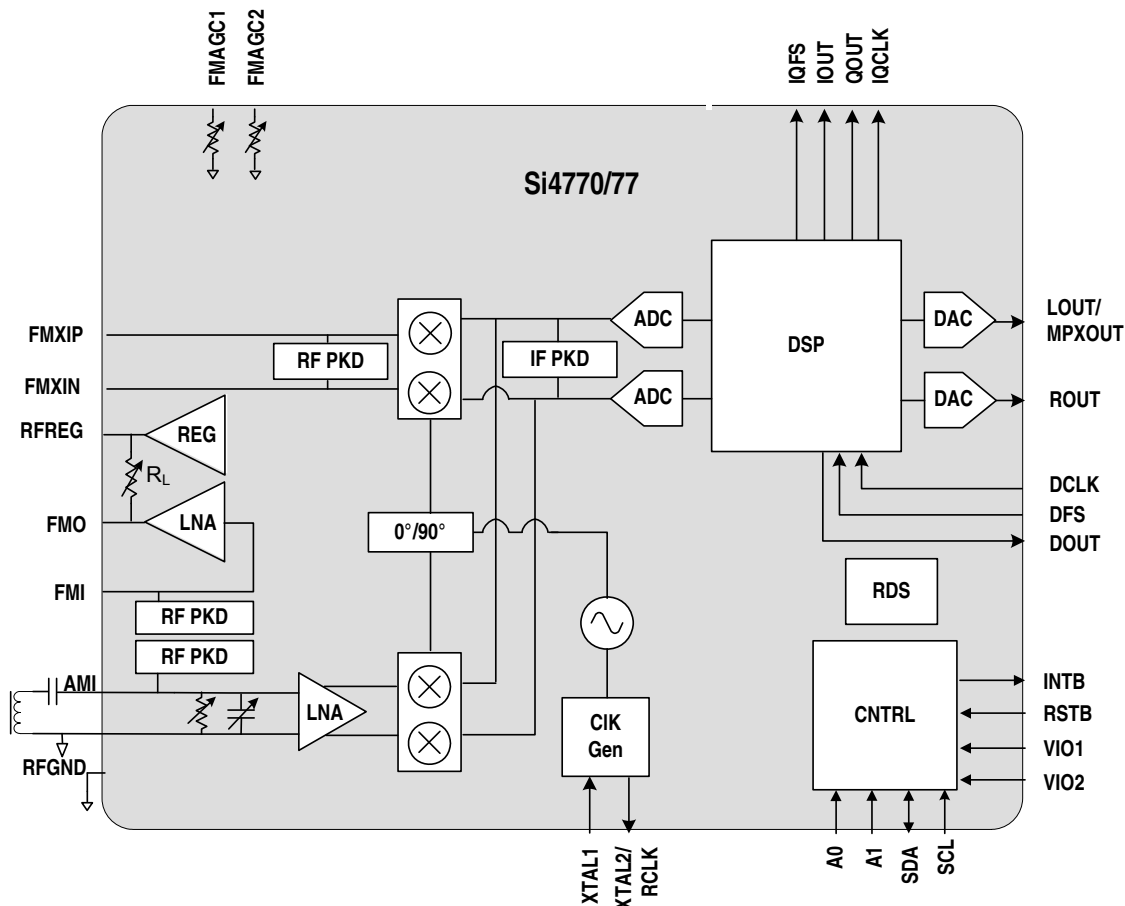
Item	Qty	Ref	Package	Value	Mfr	Part Number
1	1	T2	Transformer, Thru-hole		Silicon Laboratories	SL755TF01
2	1	T1	BALUN, 1:1, Toko		Toko	458PT1566
3	2	C13, C21	CAP, SM, 0402	0.1 $\mu$ F	Murata	GRM155R71A204KA01D
5	1	C1	CAP, SM, 0402	100 pF	Murata	GRM1555C1H101JZ01
6	1	C10	CAP, SM, 0402	18 pF	Murata	GRM1555C1H180JZ01
7	1	C8	CAP, SM, 0402	1 nF	Murata	GRM155R61H102KA01
8	5	C2, C3, C4, C5, C7	CAP, SM, 0402	2.2 nF	Murata	GRM155R71H222KA01
9	1	C9	CAP, SM, 0402	62 pF	Murata	GRM1555C1H620JD01
10	2	C6, C20	CAP, SM, 0603	10 $\mu$ F	Digikey	490-3896-2-ND
11	1	J1	CONN, SMA, Edgemount		AEP Connectors	
12	1	JP1	CONN, TH, HEADER, .100 PITCH,1X2		Samtec	HTSW-101-07-G-D
13	2	D1, D3	ESD Protector, SM		TE Connectivity	PESD0402-140
14	1	U1	IC, SM, Si4770/77-A20, QFN40		Silicon Laboratories	Si4770/77
15	1	L9	IND, SM, 0603	10 nH	Murata	
16	1	L3	IND, SM, 0603	150 nH	Murata	LQW18ANR15G00
17	1	L1	IND, SM, 0603	220 nH	Murata	LQW18ANR22G00
18	1	L2	IND, SM, 0603	47 nH	Murata	LQW18AN47NG00
21	1	X1	XTAL, SM, 3.2 x 2.5 mm	See Table 12	See Table 12	See Table 12

**Table 12. Crystal Options**

Frequency (MHz)	Mfr	Series	P/N
36.400000	NDK	NX3225SA	EXS00A-CS02420
37.800000	NDK	NX3225SA	EXS00A-CS02421
37.209375	NDK	NX3225SA	EXS00A-CS02422
36.400000	TaiSaw	SMD 3.2x2.5 36.4 MHz Crystal Unit	TZ1514A
37.800000	TaiSaw	SMD 3.2x2.5 37.8 MHz Crystal Unit	TZ1517A
37.209375	TaiSaw	SMD 3.2x2.5 37.209375 MHz Crystal Unit	TZ1522A
36.400000	Jauch	JXE115	Q36,40-JAS32P4-12-10/20-T1-LF
37.800000	Jauch	JXE115	Q37,80-JAS32P4-12-10/20-T1-LF
37.209375	Jauch	JXE115	Q37,209375-JAS32P4-12-10/20-T1-LF
36.400000	Epson Toyocom	TSX-3225	OUTD-2B-0541
37.800000	Epson Toyocom	TSX-3225	OUTD-2B-0541
37.209375	Epson Toyocom	TSX-3225	OUTD-2B-0541

## 4. Functional Description

### 4.1. Overview



**Figure 7. Si4770/77-A20 Block Diagram**

The Si4770/77-A20 radio receiver family employs 100% RF CMOS technology to bring outstanding receiver performance to the consumer electronics industry. The Si4770/77-A20 receiver family supports worldwide radio reception. The Si4770/77-A20 incorporates a digital pre-processor for the European Radio Data System (RDS) and the North American Radio Broadcast Data System (RBDS) including all required symbol decoding, block synchronization, error detection, and error correction functions. The Si4777 supports AM/FM HD radio channel reception with digital (I<sup>2</sup>S) Zero-IF (ZIF) I/Q outputs for interface to an HD radio processor.

The family leverages Silicon Laboratories' patented low-IF digital architecture, delivering superior RF performance and interference rejection. The low-IF architecture delivers superior performance while integrating the great majority of external components required by competing solutions.

The proven digital techniques provide excellent sensitivity in weak signal environments and superb selectivity and intermodulation immunity in strong signal environments. The solution offers dynamic AM/FM channel bandwidth control, auto-calibrated digital tuning, and proven AM/FM seek functionality based on multiple signal quality and band parameters. The family offers highly flexible and advanced audio processing including programmable softmute, FM stereo-mono blend, dynamic AM/FM channel bandwidth, AM/FM hi-cut, FM hi-blend, and AM lo-cut filters. In addition, the Si4770/77-A20 provides an integrated clock oscillator or accepts a reference clock and an I<sup>2</sup>C-compatible, 2-wire control interface. The Si4770/77-A20 receiver system specifies a minimal bill of materials, resulting in a small board space requirement and making the solution ideal for any consumer electronics application from single tuner radios to multiple tuner radios.



Table 13. Part Number Descriptions

Part Number	Description	FM (64–108 MHz)	MW (520–1710 kHz)	RDS	Analog MPX (VICS/DARC)	IBOC Blend	Digital ZIF (HD/DRM)	Channel EQ	IR Cal
Si4770	AM/FM RDS, VICS	✓	✓	✓	✓			✓	✓
Si4777	AM/FM RDS, VICS, HD Tuner	✓	✓	✓	✓	✓	✓	✓	✓

## 4.2. Clocking

The Si4770/77-A20 generates all internal clocking from an external crystal using an on-chip oscillator or an external programmable reference clock. The reference clock of Si4770/77-A20 is a sinusoidal or rectangular clock provided by an external source on pin RCLK. The supported crystal and external clock source frequencies are selected frequencies in the 36–38 MHz range.

The power up command enables the selection of an external crystal or reference clock. The reference clock and/or crystal accuracy should be  $\pm 100$  ppm. In a multi-receiver system, a single crystal can be shared between all Si4770/77-A20 receivers. The Si4770/77-A20 family features programmable loading capacitors for the on-chip crystal oscillator, eliminating external loading capacitors.

## 4.3. Tuning

The Si4770/77-A20 includes a complete on-chip PLL-VCO frequency synthesizer to generate the quadrature LO input to the image-reject AM and FM mixers. The Si4770/77-A20 employs a single-conversion mix (down conversion) to a fixed low IF center frequency. An innovative high-performance image reject mixer architecture allows for IF center frequencies below 300 kHz, thereby eliminating ceramic filters required in 10.7 MHz IF tuner architectures. The tune command automatically programs the LO frequency to the center of the desired channel plus (minus) the output center IF frequency when using a high-side (low-side) mix. The Si4770/77-A20 supports 50, 100, or 200 kHz channel spacing for FM, 9 or 10 kHz for AM.

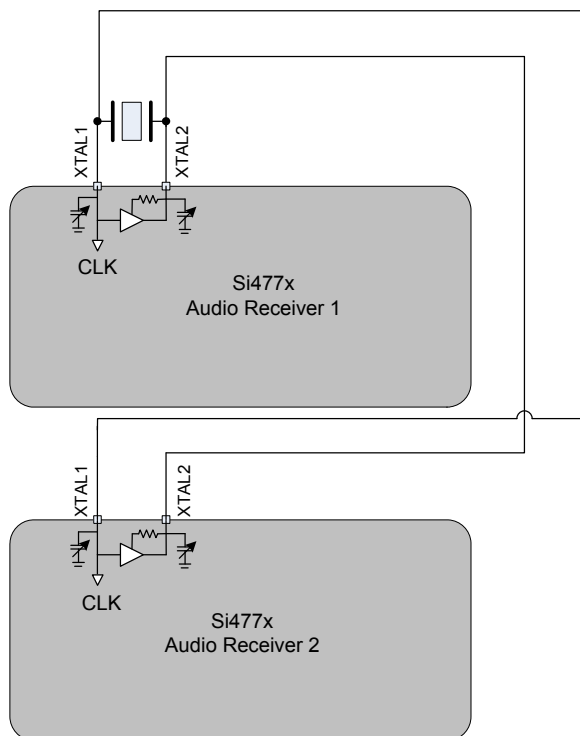


Figure 8. Xtal Share between Two Tuners